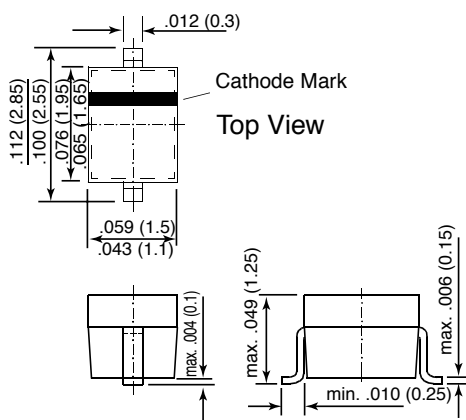


# SD106WS

## SCHOTTKY DIODES

**SOD-323**

Dimensions in inches and (millimeters)

**FEATURES**

- ◆ Low turn-on voltage
- ◆ Fast switching
- ◆ Microminiature plastic package
- ◆ These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharge.
- ◆ Ideal for protection of MOS devices, steering, biasing, and coupling diodes for fast switching and low logic level applications.

**MECHANICAL DATA****Case:** SOD-323 Plastic Package**Weight:** approx. 0.004g**Marking Code:** S2**MAXIMUM RATINGS**

Ratings at 25°C ambient temperature unless otherwise specified

	SYMBOL	VALUE	UNIT
Continuous Reverse Voltage	V <sub>R</sub>	30	Volts
Forward Current	I <sub>F</sub>	200	mA
Forward Surge Current, t <sub>p</sub> = 10ms	I <sub>FSM</sub>	1.0	A
Power Dissipation T <sub>C</sub> = 25°C	P <sub>tot</sub>	250 (NOTE 1)	mW
Thermal Resistance Junction to Ambient Air	R <sub>θJA</sub>	500	°C/W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>s</sub>	-65 to + 150	°C

**NOTES:**

(1) Valid provided that electrodes are kept at ambient temperature

**ELECTRICAL CHARACTERISTICS**

Ratings at 25°C ambient temperature unless otherwise specified

	SYMBOL	MIN.	TYP.	MAX.	UNIT
Reverse Breakdown Voltage at I <sub>R</sub> = 100 μA	BV <sub>R</sub>	30	–	–	Volts
Leakage Current at V <sub>R</sub> = 30 V	I <sub>R</sub>	–	–	5.0	μA
Forward Voltage					
at I <sub>F</sub> = 2.0 mA	V <sub>F</sub>	–	260	–	mV
at I <sub>F</sub> = 15 mA	V <sub>F</sub>	–	320	–	mV
at I <sub>F</sub> = 100 mA	V <sub>F</sub>	–	420	–	mV
at I <sub>F</sub> = 200mA	V <sub>F</sub>	–	490	550	mV
Junction Capacitance at V <sub>R</sub> = 10V, f = 1.0MHz	C <sub>tot</sub>	–	–	Max 15	pF